

FEATURES

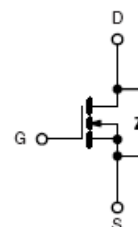
High density cell design for low $R_{DS(ON)}$
Voltage controlled small signal switch
Rugged and reliable
High saturation current capability

V_{DSS} 30 V
 I_D 5.8 A
 $R_{DS(ON)}$ 23 m Ω

3400



Equivalent Circuit



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Maximum ratings ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	5.8	A
Drain Current-Pulsed (note 1)	I_{DM}	30	A
Power Dissipation	P_D	1.5	W
Thermal Resistance from Junction to Ambient (note 2)	$R_{\theta JA}$	357	$^{\circ}\text{C}/\text{W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^{\circ}\text{C}$

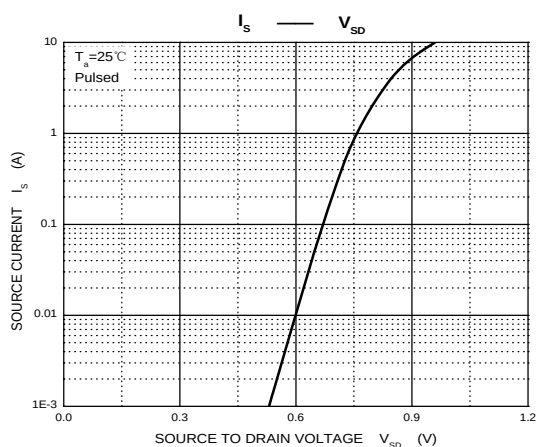
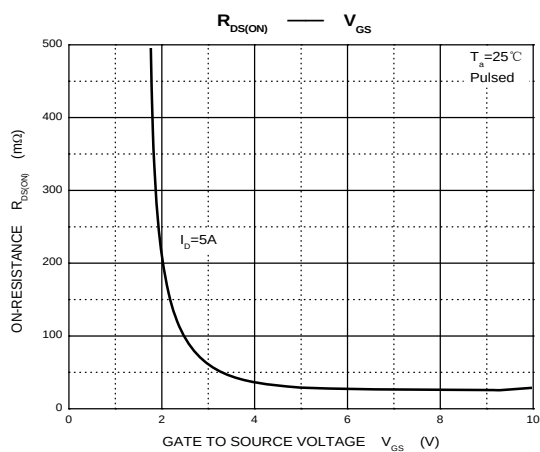
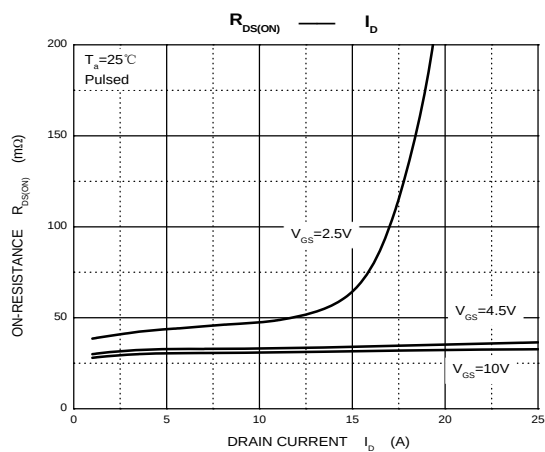
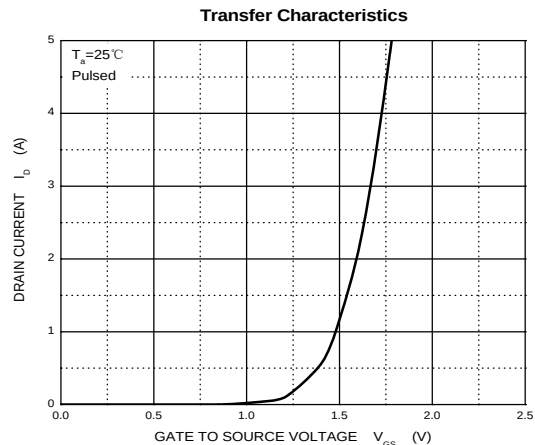
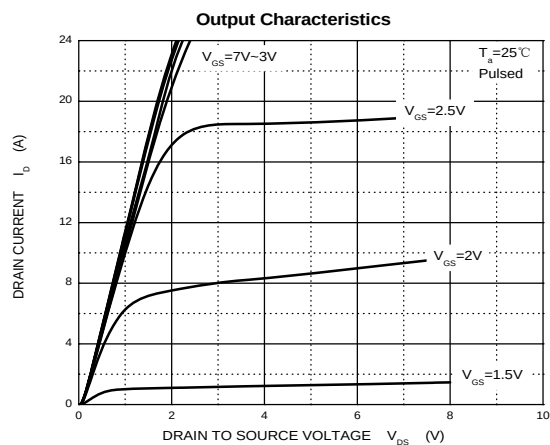
Electrical characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 24V, V_{GS} = 0V$			1	μA
Gate-source leakage current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0V$			± 100	nA
On characteristics						
Drain-source on-resistance (note 3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 5.8A$		23	28	m Ω
		$V_{GS} = 4.5V, I_D = 5A$			38	m Ω
		$V_{GS} = 2.5V, I_D = 4A$			52	m Ω
Forward tranconductance	g_{FS}	$V_{DS} = 5V, I_D = 5A$	8			S
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.7		1.4	V
Dynamic Characteristics (note 4,5)						
Input capacitance	C_{iss}	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$			1050	pF
Output capacitance	C_{oss}			99		pF
Reverse transfer capacitance	C_{rss}			77		pF
Gate resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$			3.6	Ω
Switching Characteristics (note 4,5)						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = 10V, V_{DS} = 15V,$ $R_L = 2.7\Omega, R_{GEN} = 3\Omega$			5	ns
Turn-on rise time	t_r				7	ns
Turn-off delay time	$t_{d(off)}$				40	ns
Turn-off fall time	t_f				6	ns
Drain-source diode characteristics and maximum ratings						
Diode forward voltage (note 3)	V_{SD}	$I_S = 1A, V_{GS} = 0V$			1	V

Note :

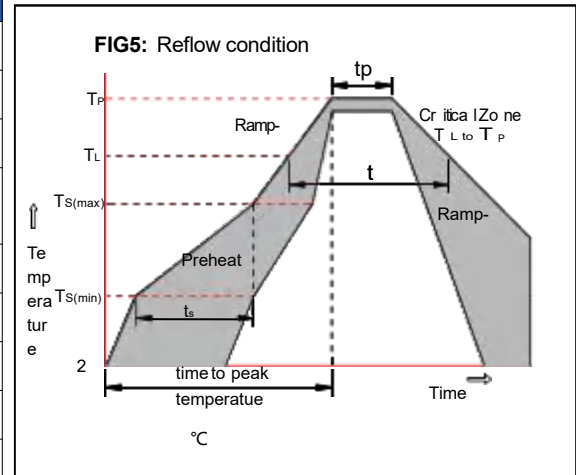
1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t < 5$ sec.
3. Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production testing.

RATING AND CHARACTERISTIC CURVES



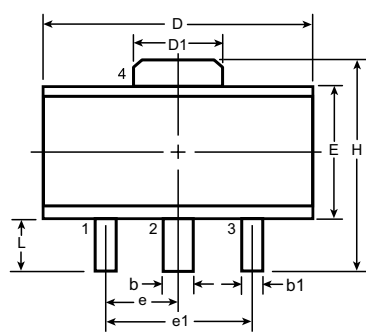
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150 °C
	-Temperature Max($T_{s(max)}$)	+200 °C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3 °C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3 °C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217 °C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5) °C
Time within 5 °C of actual Peak Temp (t_P)		30 secs. Max
Ramp-down Rate		6 °C/sec. Max
Time 25 °C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260 °C

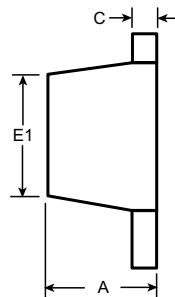


Package Dimensions & Suggested Pad Layout

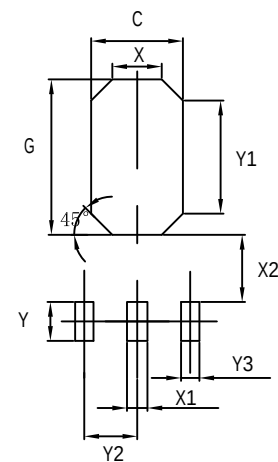
SOT89



Top View



Side View

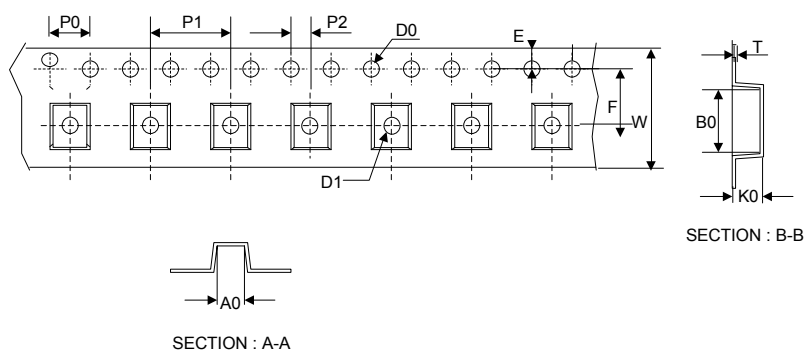


Symbol	A	b	b1	C	D	D1	E	E1	e	e1	H	L
MIN	1.40	0.44	0.36	0.3	4.40	1.50	2.29	2.00*	1.50	3.00	3.94	0.89
NOM	-	-	-	-	-	-	-	-	-	-	-	-
MAX	1.60	0.56	0.48	0.5	4.60	1.75	2.60	2.29	-	-	4.25	1.20

Dimensions	Value (in mm)
C	2.50
G	3.60
X	1.40
X1	0.90
X2	0.90
Y	1.40
Y1	2.60
Y2	1.50
Y3	0.90

Tape & rell specification

Tape



Symbol	Dimension (mm)
P0	4.00±0.20
P1	8.00±0.20
P2	2.00±0.20
D0	1.60±0.20
D1	1.60±0.20
E	1.75±0.20
F	7.50±0.15
W	16.00±0.20
A0	6.30±0.20
B0	8.25±0.20
K0	2.60±0.20
T	0.23±0.10
D2	180.0±5.0
D3	60Min.
D4	R32.0±2.0
G	R86.5±2.0
H	R30.0±2.0
I	13.0±2.0
W1	13.20±2.0
W2	16.50±2.0

Quantity: 1000PCS

13" Reel

